

10052924-060702

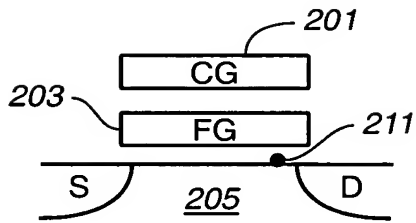


FIG. 2A

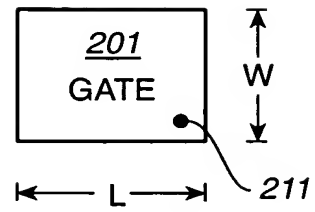


FIG. 2B

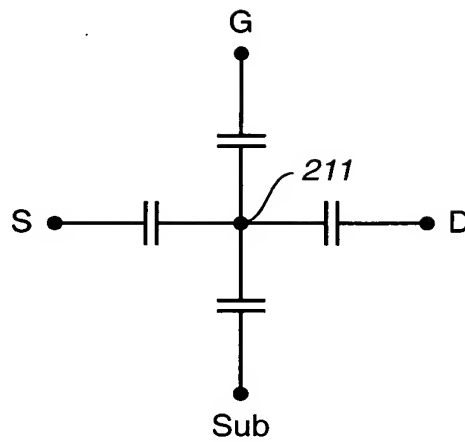


FIG. 2C

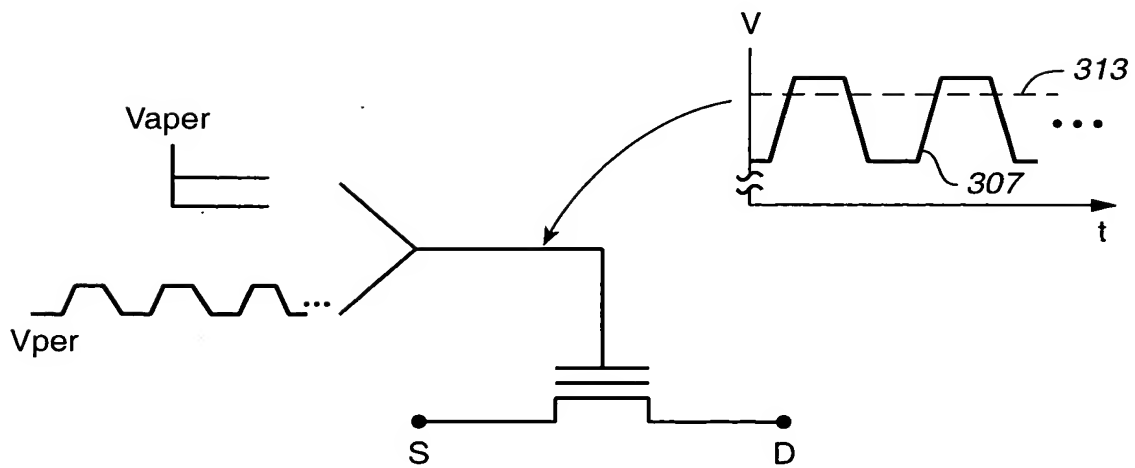
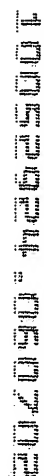


FIG. 3

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A cross-sectional view of a semiconductor device. The device features a substrate with a wavy surface. On top of the substrate, there are two regions labeled "LEFT FLOATING GATE CHANNEL" (761) and "RIGHT FLOATING GATE CHANNEL" (763), separated by a "TRANSFER CHANNEL" (762). The device includes several layers and structures: "POLY 3 (SG1) 720" is a top layer; "POLY 2 (CGL2) 771" is a layer below it; "POLY 1" is a layer below that. "N+" regions (711, 712) are located in the substrate. "FGL12" (781) and "FGR12" (783) are floating gate electrodes. "T12" (772) and "CGR2" (773) are control gate electrodes. "799" is a contact point. "762" is the transfer channel. "761" and "763" are the floating gate channels.

FIG._4B

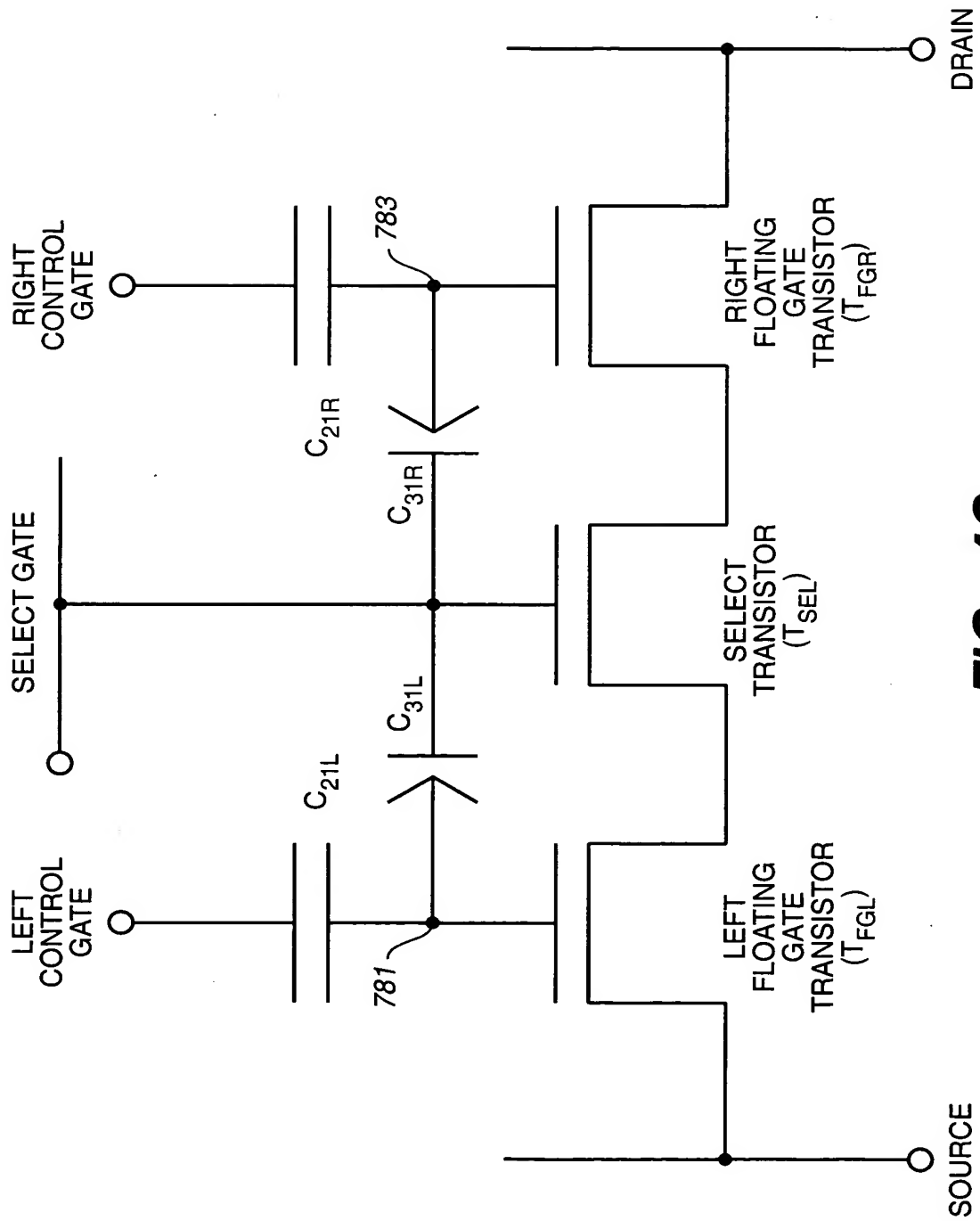


FIG. 4C

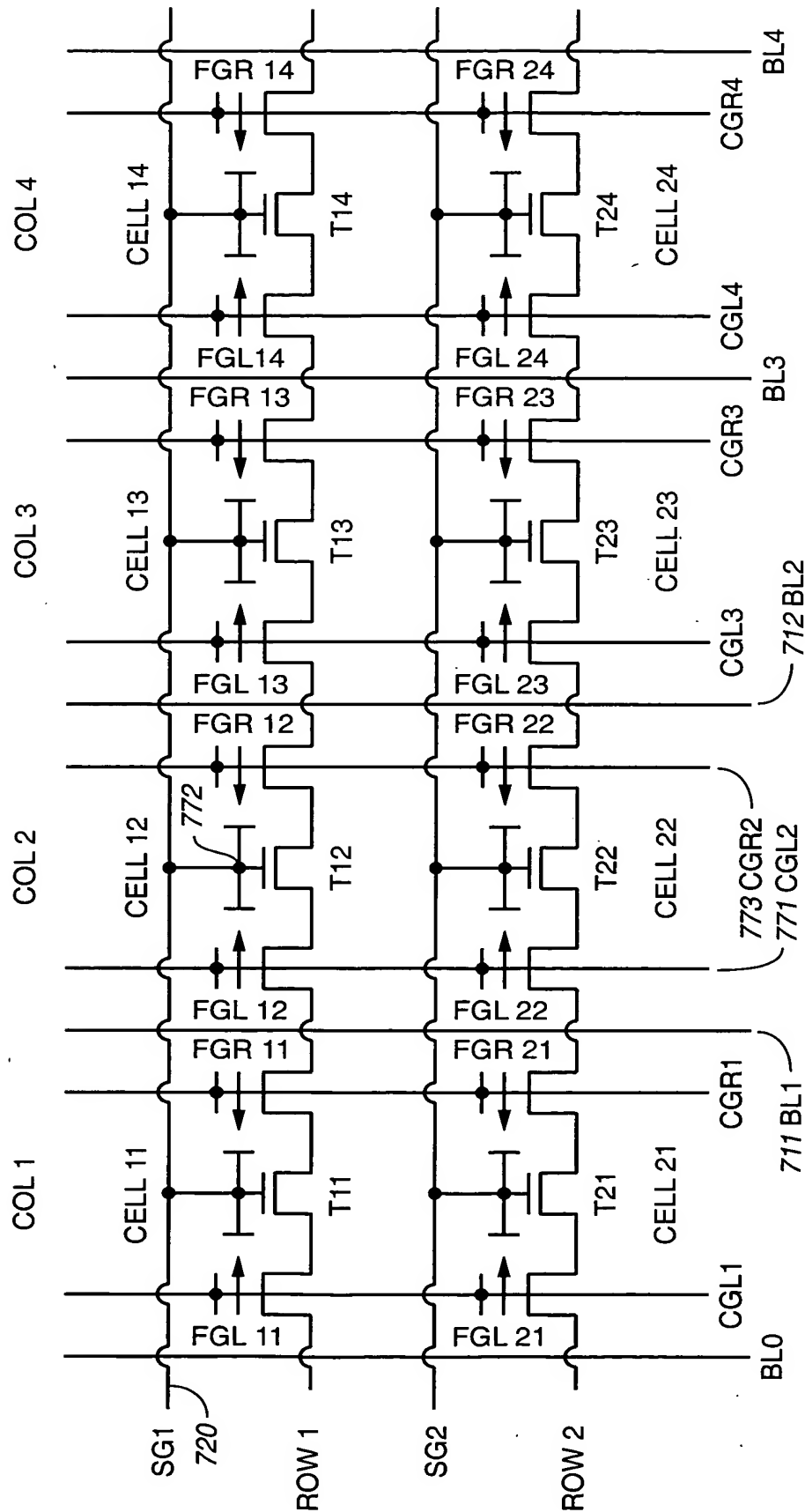


FIG. 4D

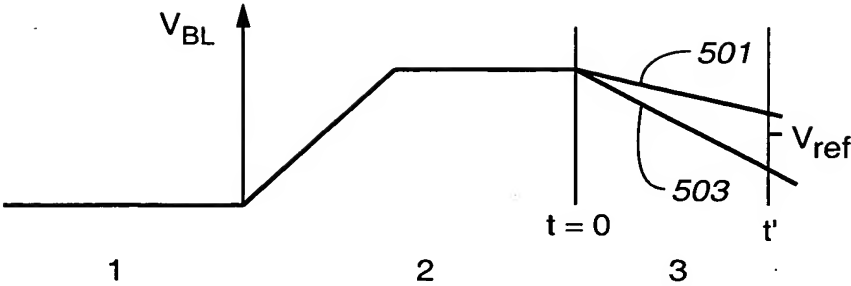


FIG. 5A

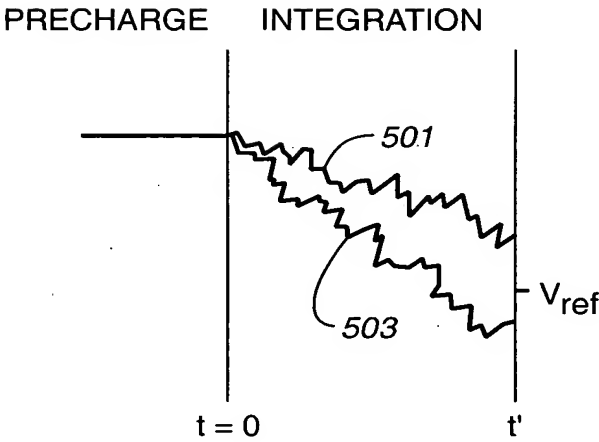


FIG. 5B

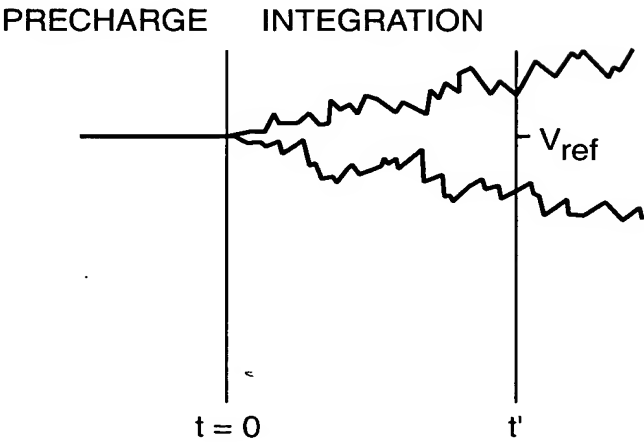


FIG. 5C

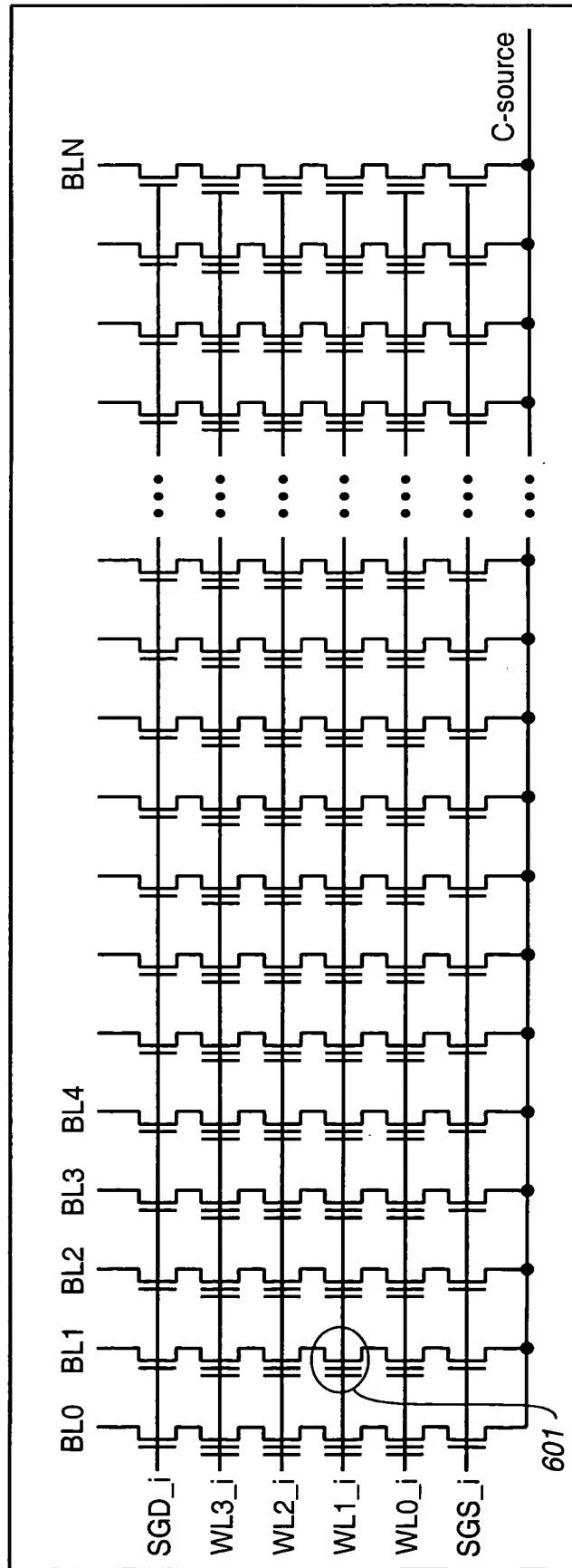
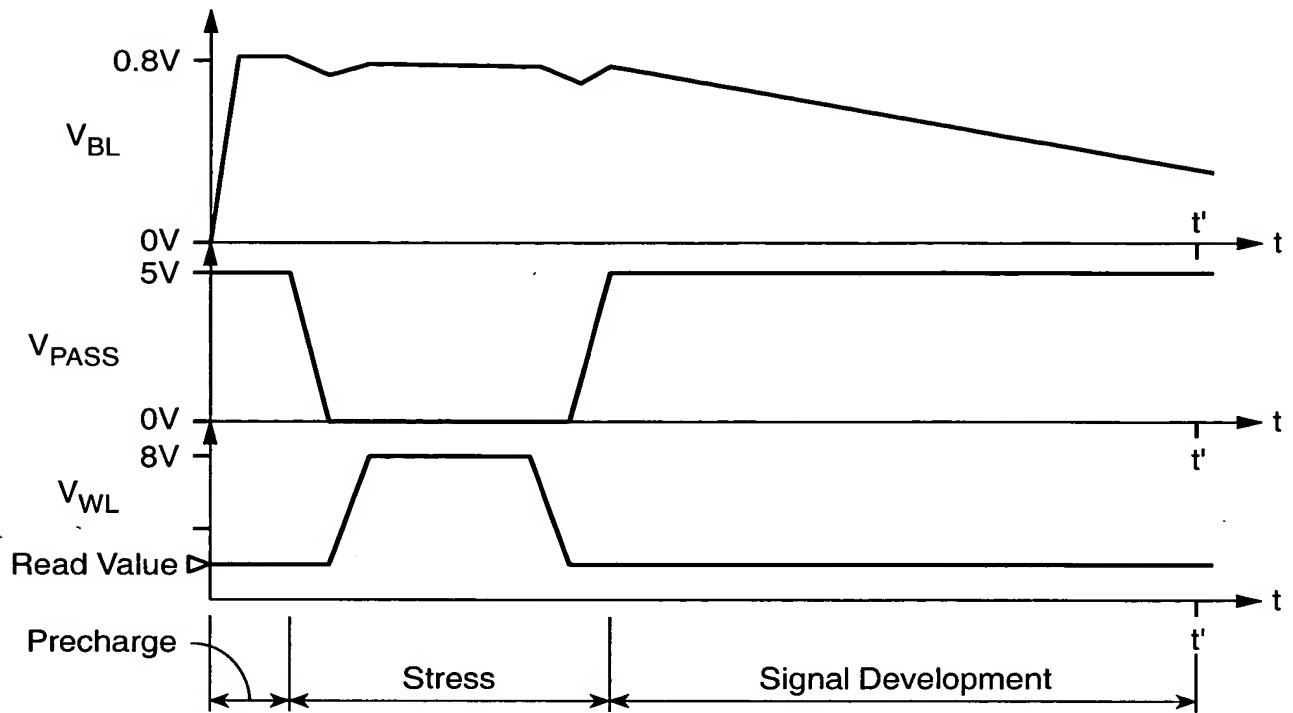
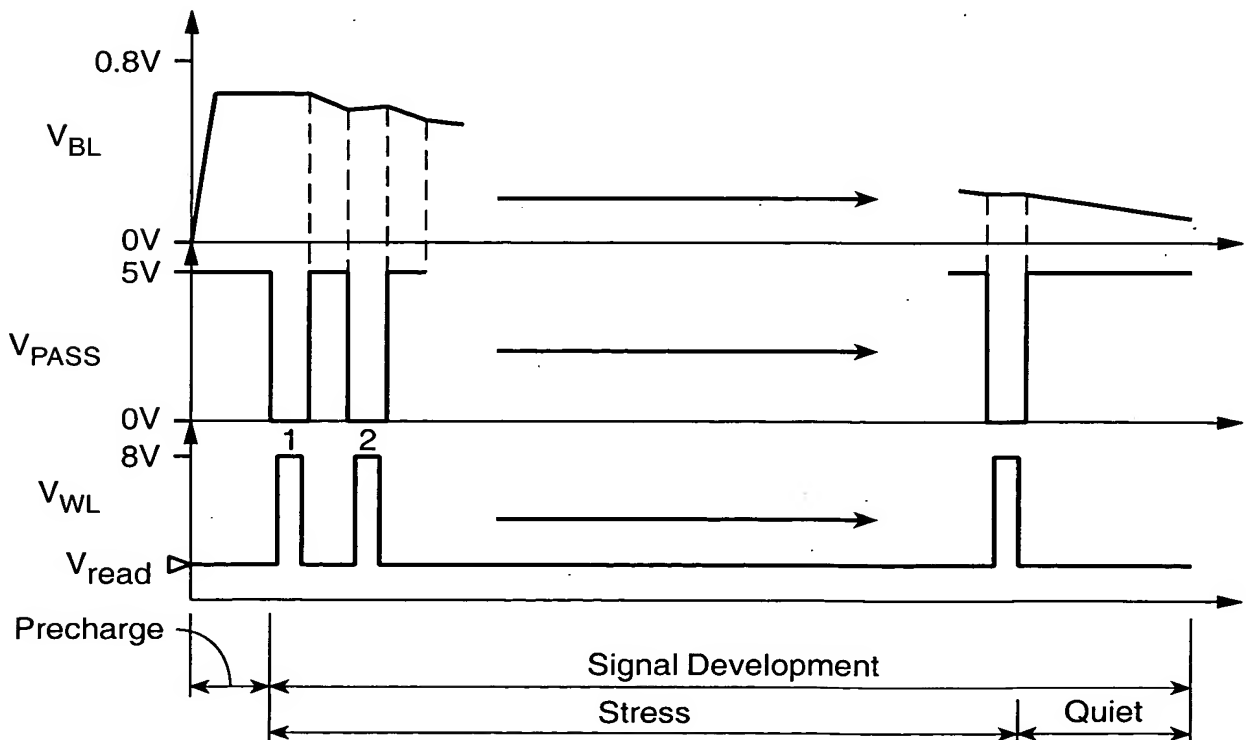
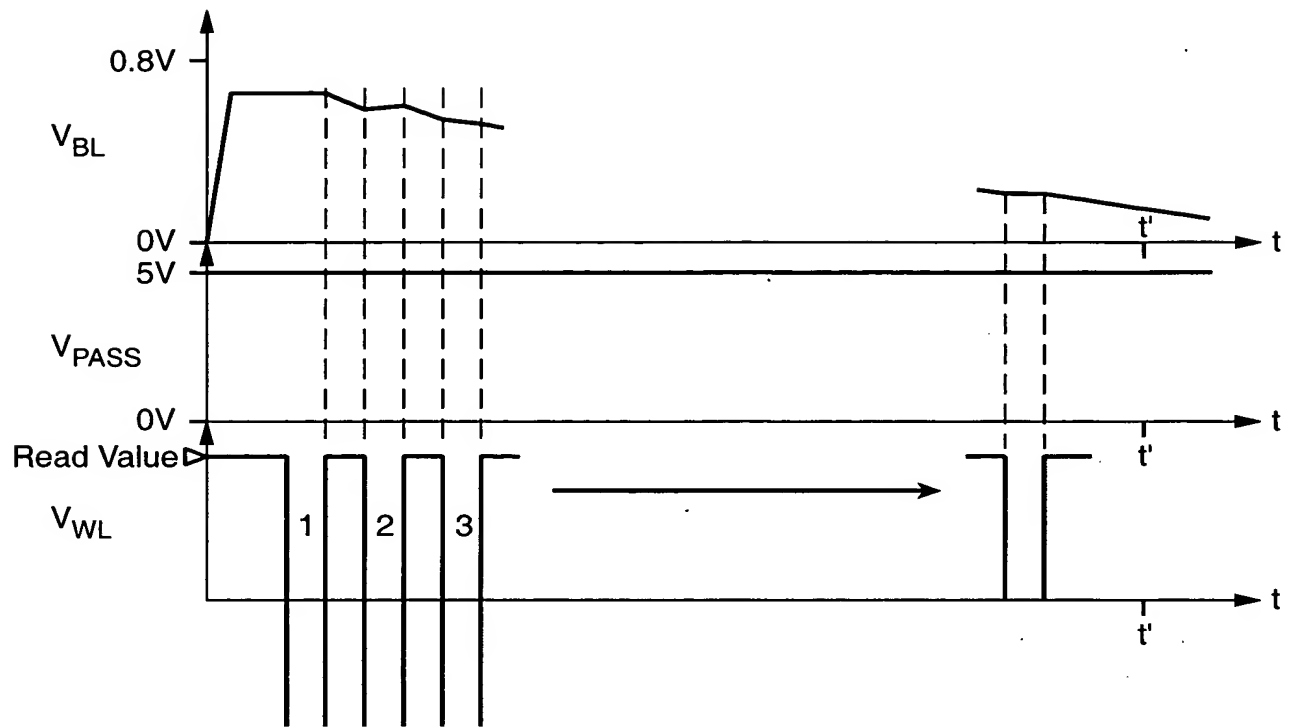


FIG.-6

**FIG. 7A****FIG. 7B**

**FIG._7C**

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